

# G3R160MT12D

## 1200 V 160 mΩ SiC MOSFET



Silicon Carbide MOSFET  
N-Channel Enhancement Mode

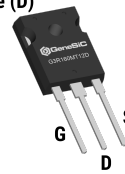
V <sub>DS</sub>	=	1200 V
R <sub>DS(ON)(Typ.)</sub>	=	160 mΩ
I <sub>D</sub> (T <sub>c</sub> = 100°C)	=	15 A

### Features

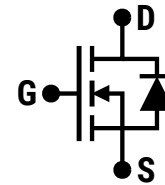
- G3R™ Technology - +15 V / -5 V Gate Drive
- Superior Q<sub>G</sub> x R<sub>DS(ON)</sub> Figure of Merit
- Low Capacitances and Low Gate Charge
- Normally-Off Stable Operation up to 175°C
- Fast and Reliable Body Diode
- High Avalanche and Short Circuit Ruggedness
- Low Conduction Losses at High Temperatures

### Package

Case (D)



**TO-247-3**



D = Drain  
G = Gate  
S = Source



### Advantages

- Increased Power Density for Compact System
- High Frequency Switching
- Reduced Losses for Higher System Efficiency
- Minimized Gate Ringing
- Improved Thermal Capability
- Superior Cost-Performance Index
- Ease of Paralleling without Thermal Runaway
- Simple to Drive

### Applications

- Solar Inverters
- UPS
- High Voltage DC-DC Converters
- Switched Mode Power Supplies
- Auxiliary Motor Drives
- High Frequency Converters

### Absolute Maximum Ratings (At T<sub>c</sub> = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Drain-Source Voltage	V <sub>DS(max)</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 100 μA	1200	V	
Gate-Source Voltage (Dynamic)	V <sub>GS(max)</sub>		-10 / +20	V	
Gate-Source Voltage (Static)	V <sub>GS(op)</sub>	Recommended Operation	-5 / +15	V	
Continuous Forward Current	I <sub>D</sub>	T <sub>c</sub> = 25°C, V <sub>GS</sub> = -5 / +15 V	22	A	Fig. 15
		T <sub>c</sub> = 100°C, V <sub>GS</sub> = -5 / +15 V	15		
		T <sub>c</sub> = 135°C, V <sub>GS</sub> = -5 / +15 V	11		
Pulsed Drain Current	I <sub>D(pulse)</sub>	t <sub>p</sub> ≤ 10 μs, D ≤ 1%, Note 1	40	A	Fig. 14
Power Dissipation	P <sub>D</sub>	T <sub>c</sub> = 25°C	123	W	Fig. 16
Operating and Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>		-55 to 175	°C	

### Thermal/Package Characteristics

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Thermal Resistance, Junction - Case	R <sub>thJC</sub>			0.94	1.22	°C/W	Fig. 13
Weight	W <sub>T</sub>			6.1		g	
Mounting Torque	T <sub>M</sub>	Screws to Heatsink			1.1	Nm	

Note 1: Pulse Width t<sub>p</sub> Limited by T<sub>j(max)</sub>

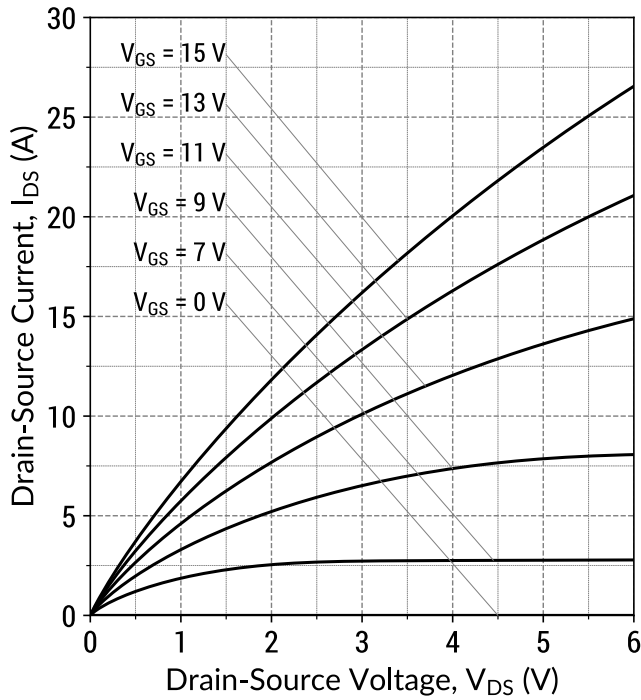
**Electrical Characteristics** (At  $T_c = 25^\circ\text{C}$  Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{DSS}$	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	1200			V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$		1		$\mu\text{A}$	
Gate Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = -10\text{ V}$			-100		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 5.0\text{ mA}$		2.69		V	Fig. 9
		$V_{DS} = V_{GS}, I_D = 5.0\text{ mA}, T_j = 175^\circ\text{C}$		2.05			
Transconductance	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$		4.0		S	Fig. 4
		$V_{DS} = 10\text{ V}, I_D = 10\text{ A}, T_j = 175^\circ\text{C}$		4.5			
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 15\text{ V}, I_D = 10\text{ A}$		160	192	mΩ	Fig. 5-8
		$V_{GS} = 15\text{ V}, I_D = 10\text{ A}, T_j = 175^\circ\text{C}$		220			
Input Capacitance	$C_{iss}$			730		pF	Fig. 11
Output Capacitance	$C_{oss}$			28			
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$		4.5			
$C_{oss}$ Stored Energy	$E_{oss}$			11		$\mu\text{J}$	Fig. 12
$C_{oss}$ Stored Charge	$Q_{oss}$			40		nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 800\text{ V}, V_{GS} = -5 / +15\text{ V}$		8		nC	Fig. 10
Gate-Drain Charge	$Q_{gd}$	$I_D = 10\text{ A}$		10			
Total Gate Charge	$Q_g$	Per IEC607478-4		28			
Internal Gate Resistance	$R_{G(int)}$	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$		2.0		Ω	

**Reverse Diode Characteristics**

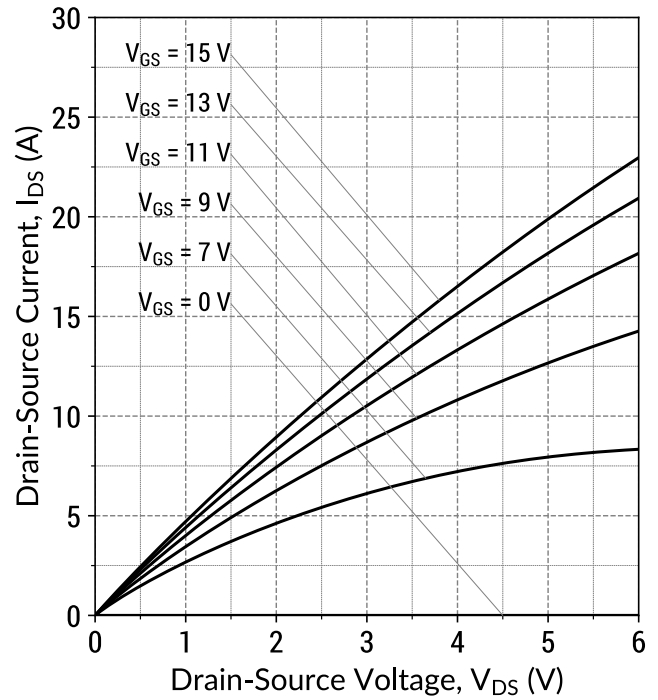
Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 5\text{ A}$		4.9		V	Fig. 17-18
		$V_{GS} = -5\text{ V}, I_{SD} = 5\text{ A}, T_j = 175^\circ\text{C}$		4.4			
Continuous Diode Forward Current	$I_S$	$V_{GS} = -5\text{ V}, T_c = 100^\circ\text{C}$	10			A	
Diode Pulse Current	$I_{S(pulse)}$	$V_{GS} = -5\text{ V}, \text{Note 1}$		40		A	

**Figure 1: Output Characteristics ( $T_j = 25^\circ\text{C}$ )**



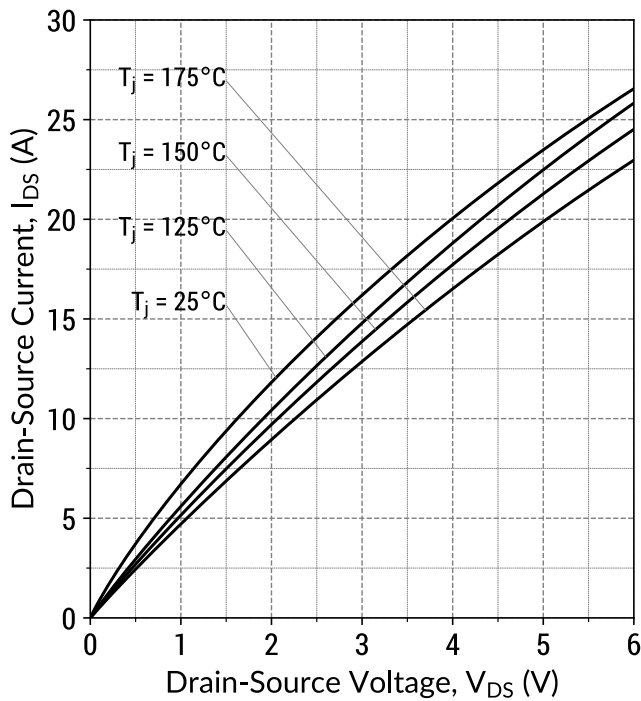
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

**Figure 2: Output Characteristics ( $T_j = 175^\circ\text{C}$ )**



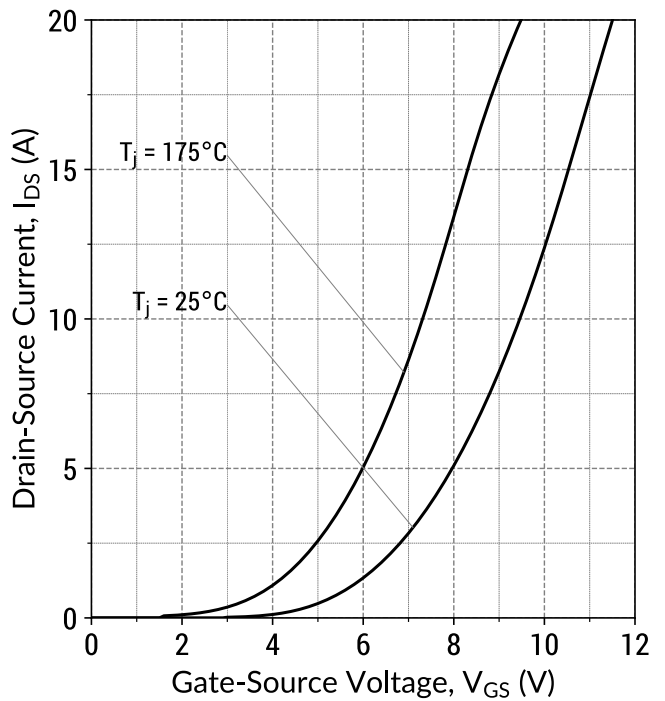
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

**Figure 3: Output Characteristics ( $V_{GS} = 15 \text{ V}$ )**



$I_D = f(V_{DS}, T_j); t_P = 250 \mu\text{s}$

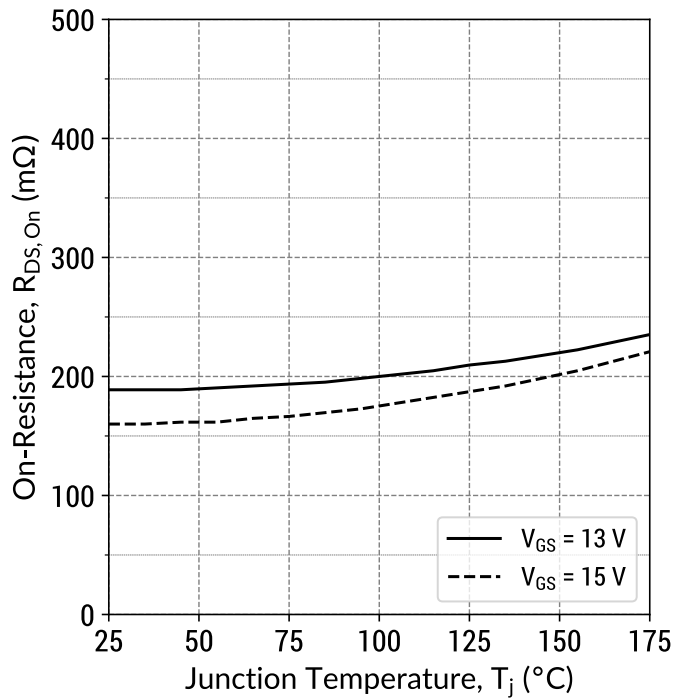
**Figure 4: Transfer Characteristics ( $V_{DS} = 10 \text{ V}$ )**



$I_D = f(V_{GS}, T_j); t_P = 100 \mu\text{s}$

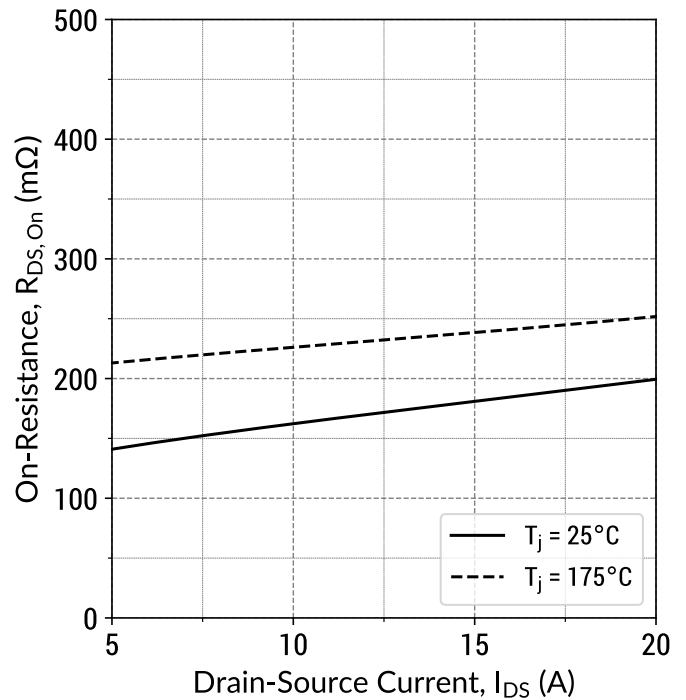


Figure 5: On-State Resistance v/s Temperature



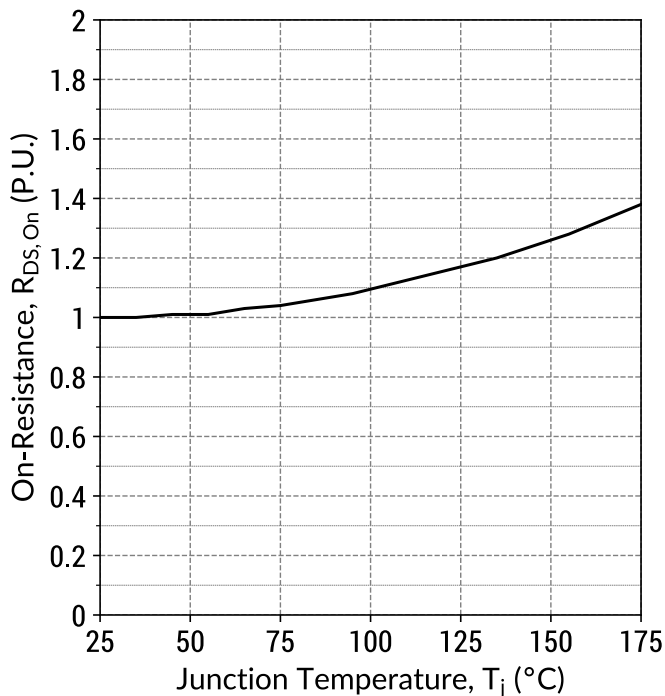
$R_{DS(ON)} = f(T_j, V_{GS}); t_P = 250\ \mu\text{s}; I_D = 10\ \text{A}$

Figure 6: On-State Resistance v/s Drain Current



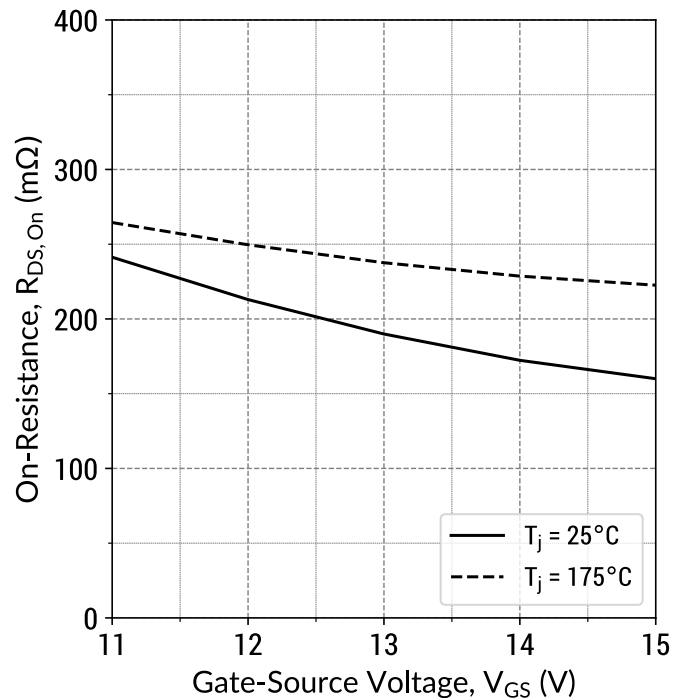
$R_{DS(ON)} = f(T_j, I_D); t_P = 250\ \mu\text{s}; V_{GS} = 15\ \text{V}$

Figure 7: Normalized On-State Resistance v/s Temperature



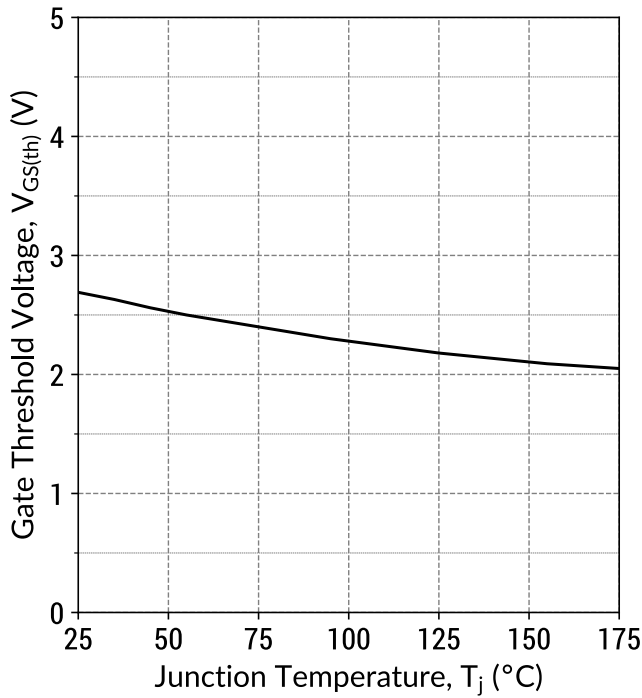
$R_{DS(ON)} = f(T_j); t_P = 250\ \mu\text{s}; I_D = 10\ \text{A}; V_{GS} = 15\ \text{V}$

Figure 8: On-State Resistance v/s Gate Voltage



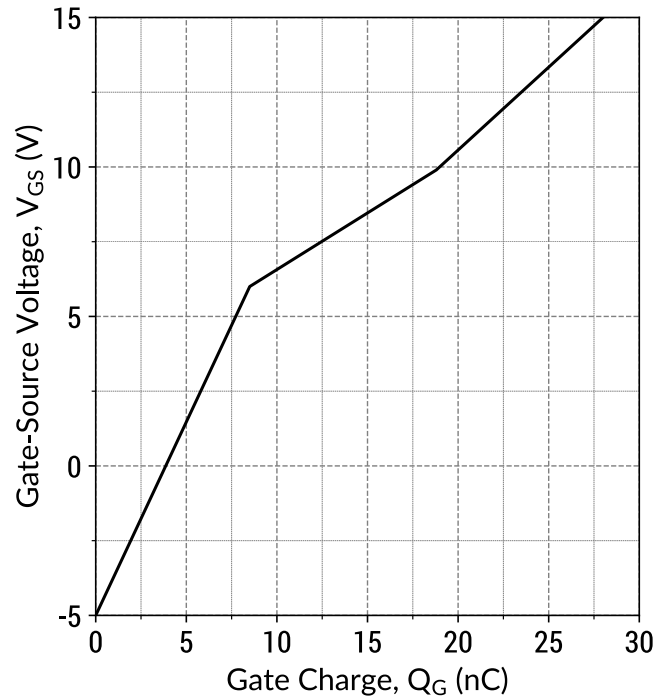
$R_{DS(ON)} = f(T_j, V_{GS}); t_P = 250\ \mu\text{s}; I_D = 10\ \text{A}$

Figure 9: Threshold Voltage Characteristics



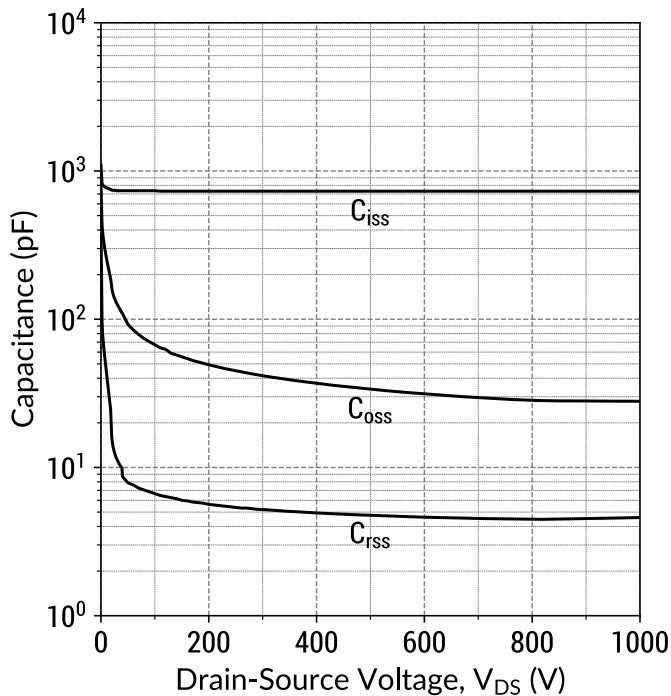
$V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 5.0 \text{ mA}$

Figure 10: Gate Charge Characteristics



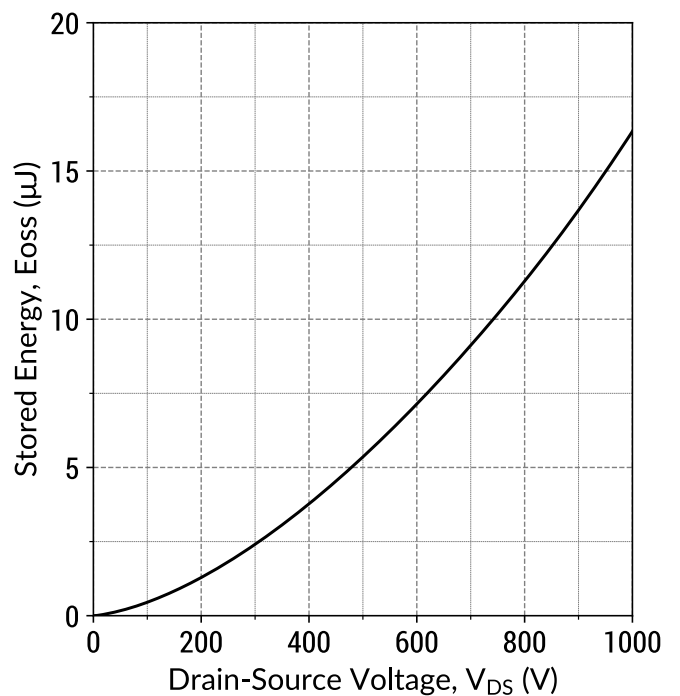
$I_D = 10 \text{ A}; V_{DS} = 800 \text{ V}; T_c = 25^\circ\text{C}$

Figure 11: Capacitance v/s Drain-Source Voltage



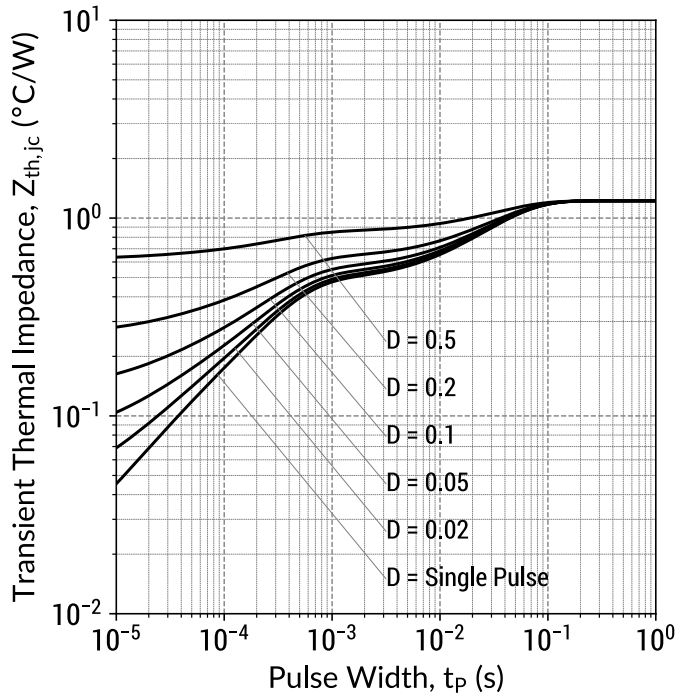
$f = 1 \text{ MHz}; V_{AC} = 25\text{mV}$

Figure 12: Output Capacitor Stored Energy



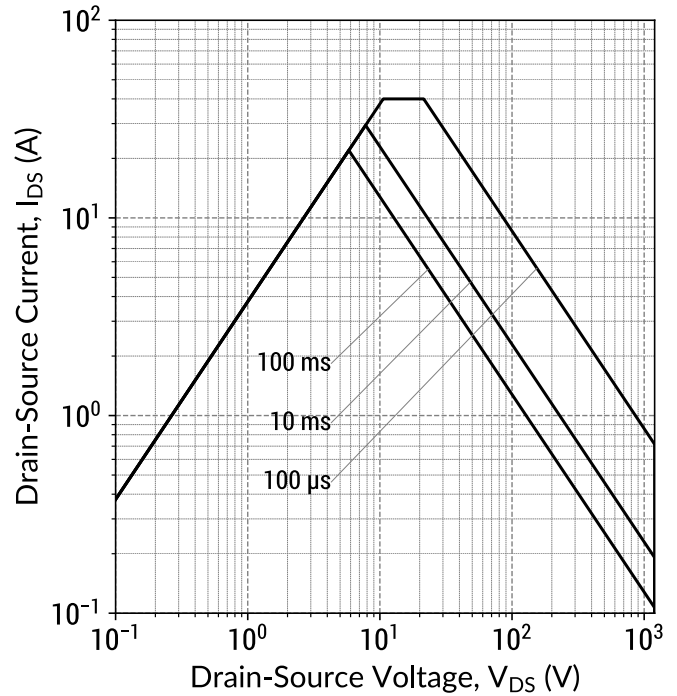
$E_{oss} = f(V_{DS})$

Figure 13: Transient Thermal Impedance



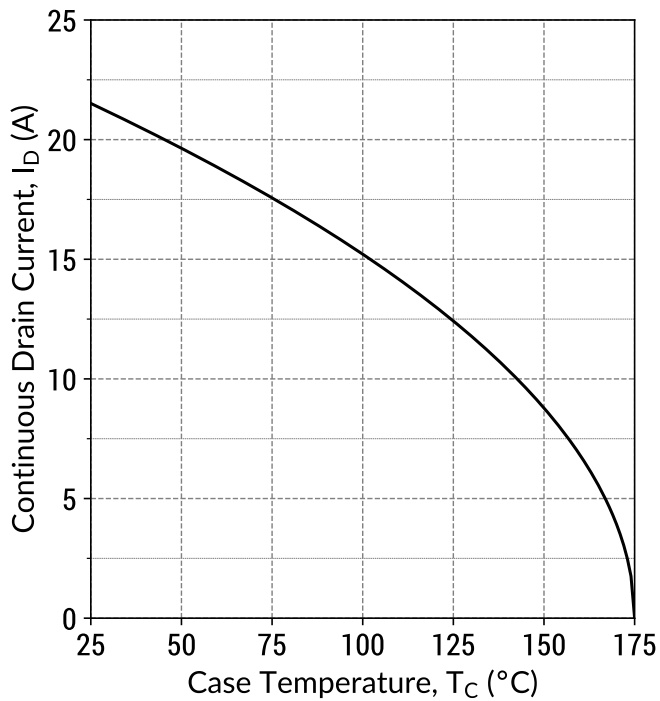
$$Z_{th,jc} = f(t_p, D); D = t_p/T$$

Figure 14: Safe Operating Area ( $T_c = 25^\circ\text{C}$ )



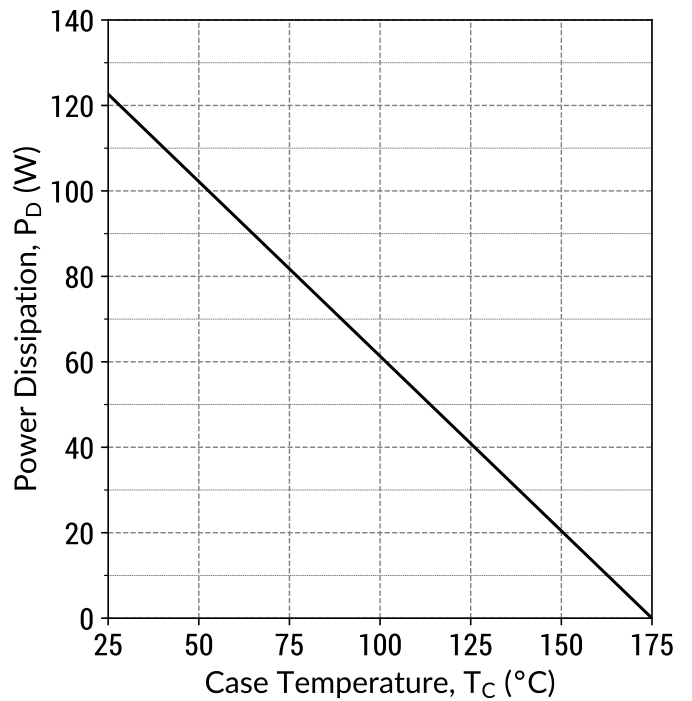
$$I_D = f(V_{DS}, t_p); T_j \leq 175^\circ\text{C}; D = 0$$

Figure 15: Current De-rating Curve



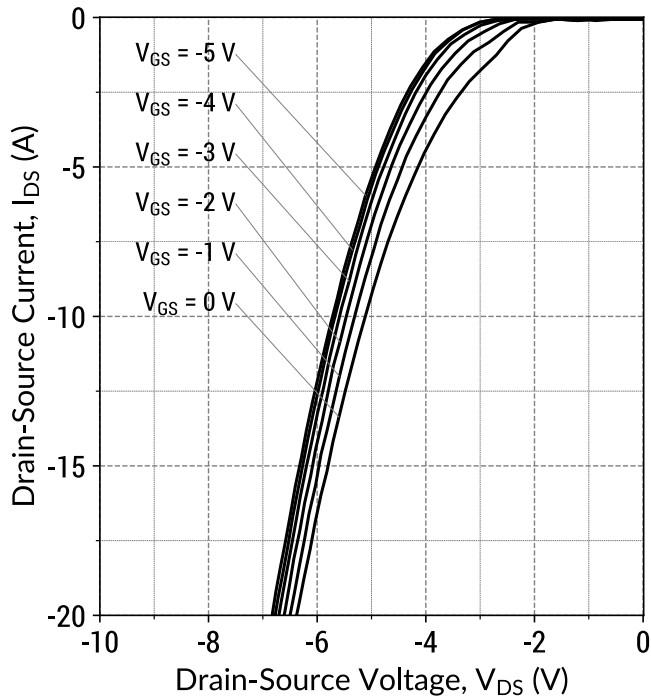
$$I_D = f(T_C); T_j \leq 175^\circ\text{C}$$

Figure 16: Power De-rating Curve



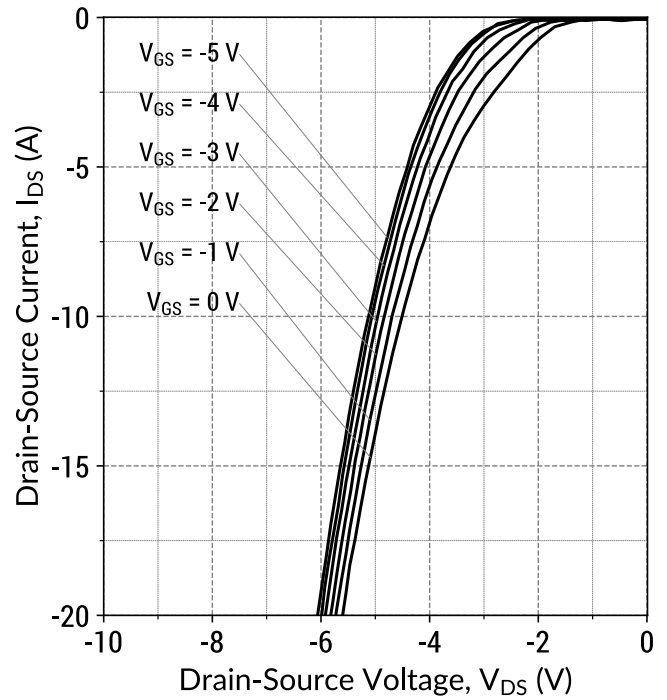
$$P_D = f(T_C); T_j \leq 175^\circ\text{C}$$

Figure 17: Body Diode Characteristics ( $T_j = 25^\circ\text{C}$ )



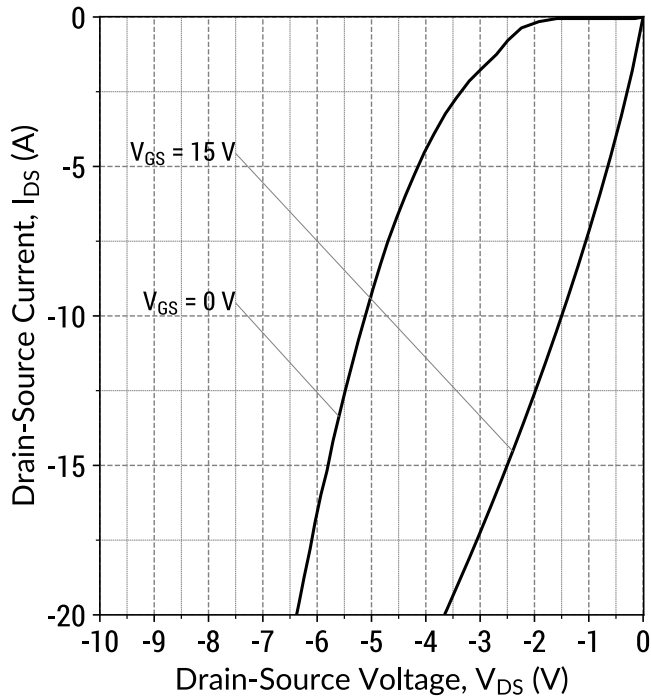
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 18: Body Diode Characteristics ( $T_j = 175^\circ\text{C}$ )



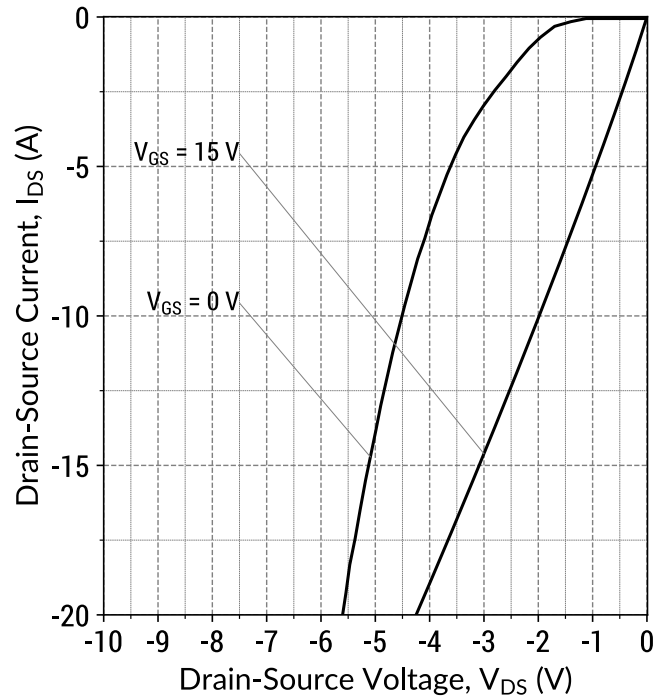
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 19: Third Quadrant Characteristics ( $T_j = 25^\circ\text{C}$ )



$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 20: Third Quadrant Characteristics ( $T_j = 175^\circ\text{C}$ )

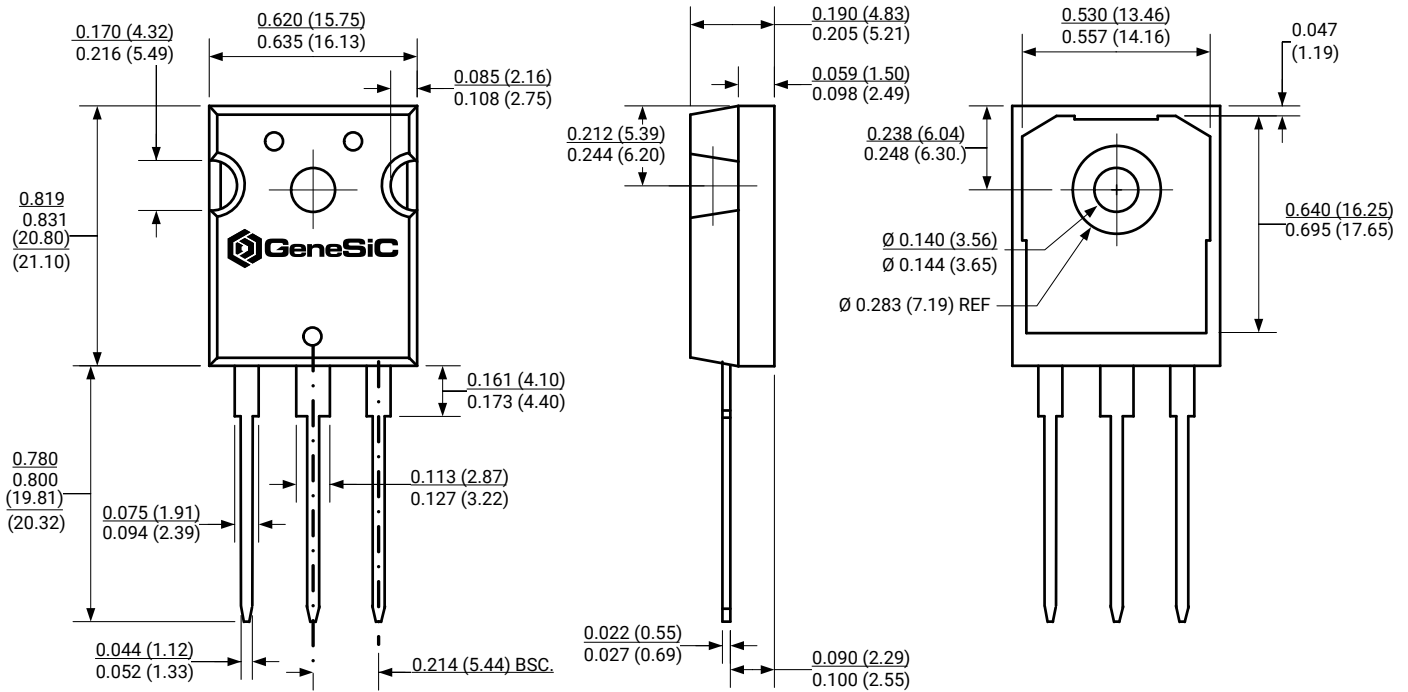


$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

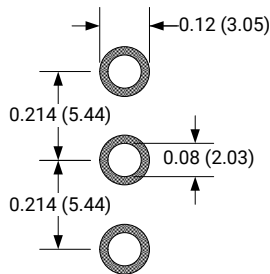


**Package Dimensions**

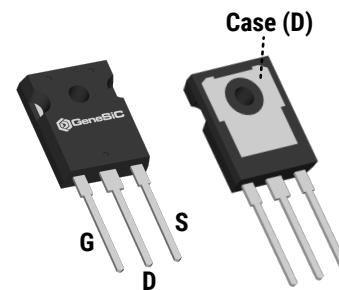
**TO-247-3 Package Outline**



**Recommended Solder Pad Layout**



**Package View**



**NOTE**

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.



## Compliance

### RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

### REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

## Disclaimer

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Unless otherwise expressly indicated, GeneSiC products are not designed, tested or authorized for use in life-saving, medical, aircraft navigation, communication, air traffic control and weapons systems, nor in applications where their failure may result in death, personal injury and/or property damage.

## Related Links

- SPICE Models: [https://www.genesicsemi.com/sic-mosfet/G3R160MT12D/G3R160MT12D\\_SPICE.zip](https://www.genesicsemi.com/sic-mosfet/G3R160MT12D/G3R160MT12D_SPICE.zip)
- PLECS Models: [https://www.genesicsemi.com/sic-mosfet/G3R160MT12D/G3R160MT12D\\_PLECS.zip](https://www.genesicsemi.com/sic-mosfet/G3R160MT12D/G3R160MT12D_PLECS.zip)
- CAD Models: [https://www.genesicsemi.com/sic-mosfet/G3R160MT12D/G3R160MT12D\\_3D.zip](https://www.genesicsemi.com/sic-mosfet/G3R160MT12D/G3R160MT12D_3D.zip)
- Gate Driver Reference: <https://www.genesicsemi.com/technical-support>
- Evaluation Boards: <https://www.genesicsemi.com/technical-support>
- Reliability: <https://www.genesicsemi.com/reliability>
- Compliance: <https://www.genesicsemi.com/compliance>
- Quality Manual: <https://www.genesicsemi.com/quality>

## Revision History

Date	Revision	Comments	Supersedes
Aug. 25, 2020	Rev 2	Recommended Gate Voltage Changed from +20 V/-5 V to +15 V/-5 V	Rev 1
Jun. 2, 2020	Rev 1	Initial Release	



[www.genesicsemi.com/sic-mosfet/](https://www.genesicsemi.com/sic-mosfet/)